A 130-147.7 GHz CMOS Low Noise Amplifier for Satellite Communication

Jeong-Taek Lim Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea jtlim@cnu.ac.kr

Min-Seok Baek Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea 202250794@o.cnu.ac.kr

Byeong Chan Lee Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea bbb0468@naver.com

Eun-Gyu Lee Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea eungyu@cnu.ac.kr Jae-Hyeok Song Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea sjh6248@o.cnu.ac.kr

Jae-Eun Lee Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea line 5: yje1128@o.cnu.ac.kr

Jong-Seong Park Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea whdtjd3564@naver.com

Sunkyu Choi Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea sgch@cnu.ac.kr Jeong-Taek Son Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea sonkkul1@o.cnu.ac.kr

Joon-Hyung Kim Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea joonh970@gmail.com

IlHun Kim Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea ilhun@g.cnu.ac.kr

Choul-Young Kim Department of Electronics Engineering Chungnam National University Daejeon, Republic of Korea cykim@cnu.ac.kr

Abstract—This study proposes a three-stage low-noise amplifier (LNA) for D-band satellite communication, where each stage has a different topology. Each stage is configured using a single-ended common-source (CS), a single-ended cascode, and a differential cascode structure to reduce the noise figure while ensuring sufficient gain and linearity. To reduce the noise figure, a large transistor technique is applied to the first stage, while the capacitive neutralization technique is applied to the third stage to enhance gain. To verify this development, a proposed LNA was implemented using 60-nm bulk CMOS technology. The core size of this LNA is 0.086 mm². Measurement results show that 16.77 dB peak gain, 6.42–7.02 dB NF. The LNA has an input 1-dB compression point (IP1dB) of -15 dBm at 130-150 GHz and the power consumption is 60 mW.

Keywords—CMOS, D-band, Low noise amplifier, Satellite communication

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